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Surge Current Capability of Ga₂O₃ Schottky Diodes

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Abstract— β -Ga₂O₃ is an attractive material to build power electronic semiconductor devices, because of its ultra-wide bandgap and the availability of large-diameter wafers growing from its own melt. However, device performance may be limited by the relatively poor thermal conductivity of the material.

In this paper, we investigate the behavior of β -Ga₂O₃ Schottky diodes in the condition of forward current surge. An analytical electro-thermal device model is calibrated with experimental devices and TCAD simulations. Then this device model is incorporated into a SPICE electro-thermal network model, which is used to simulate the device temperature rise during the surge transient, considering various device and packaging configurations (i.e. various chip thicknesses, single-side or double-side cooling).

It is found that providing heat is removed through both sides of the die, a β -Ga₂O₃ Schottky diode offers a robustness to surge current comparable to that of a SiC Schottky diode. The low thermal conductivity of β -Ga₂O₃ is found to be balanced by the enhanced heat extraction from top-side cooling as well as the intrinsic low on-resistance (and conduction loss) increase with temperature in β -Ga₂O₃ devices.

I. INTRODUCTION

From an electrical point-of-view, β -Ga₂O₃ is a very promising material. Its high critical electric field ($\approx 8 \text{ MV cm}^{-1}$) [1], in particular, makes it very attractive for power semiconductor devices. This can be summarized using the Baliga's Figure Of Merit (the product of a material permittivity, electron mobility, and critical field raised to the cubic power, $\mu\epsilon E_c^3$). The BFOM of β -Ga₂O₃ is higher than that of the main wide-bandgap semiconductor materials, at 3444 (vs. 340 and 870 for SiC and GaN, respectively) [2]. This means that devices made using β -Ga₂O₃ can offer a lower on-state resistance for a given voltage rating than those made out of Si, SiC or GaN. Several high voltage, low resistance β -Ga₂O₃ devices have already been demonstrated, such as a $2 \text{ m}\Omega \text{ cm}^2$, 1100 V diode [3].

Another advantage of β -Ga₂O₃ is material growth: contrarily to SiC and GaN, bulk, mono-crystalline β -Ga₂O₃ substrates can be produced by a variety of melt-growth process [4]. Substrates up to 100 mm in diameter are readily available, and 150 mm wafers are under development [1].

However, β -Ga₂O₃ suffers from a major drawback: its thermal conductivity is very low (11 to $27 \text{ W m}^{-1} \text{ K}^{-1}$ depending on the crystal orientation [5]), approximately 10 to 20 times lower than that of GaN or SiC. This means that the semiconductor chip has a relatively high thermal resistance, making

it much more difficult to remove heat from the semiconductor junction to a heatsink. When dissipating the same power density as a SiC device, a β -Ga₂O₃ device will run much hotter (70 °C more in an example of [6]). This may cause the device to exceed its safe operating temperature, which is limited by either the Schottky contact or the packaging materials. This also may reduce its long-term reliability due to wider thermal cycling.

A common application scenario that may cause the diode temperature to exceed its maximum junction temperature is current surge. This may happen for example when the output of a diode rectifier is short-circuited. In this case, the diode must temporarily carry a current intensity noticeably higher than what it can sustain in steady state (nominal) conditions. This surge current value is listed in a diode's datasheet, and the corresponding tests are defined in JEDEC standards [7]. One particular test use a half-sine current-pulse at the frequency of the ac electrical grid (here 50 Hz).

Current surges are transitory events which result in fast rise in the junction temperature of the diode: at one point during the current surge tests performed in [8], the junction temperature of a SiC Schottky diode was estimated to more than 800 °C. Such very high temperature transient is the result of two concomitant effects: first, the limited thermal inertia of the semiconductor chip; secondly, the positive temperature coefficient of the conduction losses, which causes the dissipated power to increase with the junction temperature, and may result in thermal runaway.

Several techniques have been developed to improve the current surge capability of semiconductor devices. Increasing the thermal inertia by clamping the semiconductor chip between two thick metal shims, for example, may results in doubling the current surge capability of a SiC diode, as compared with a more standard single-side cooling [9]. Another approach is to limit the increase in conduction losses with temperature. For SiC Schottky diodes, this is achieved by introducing bipolar junctions to form JBS (Junction Barrier Schottky) or MPS (Merged Pin Schottky) structures. This was found to improve noticeably the robustness of the diodes to thermal runaway [10].

Unfortunately, JBS or MPS structures require p-type doping and hole conduction, which are not available for β -Ga₂O₃ devices [3]. Only unipolar diodes can be made using this material. Therefore, current surge capability of these diodes

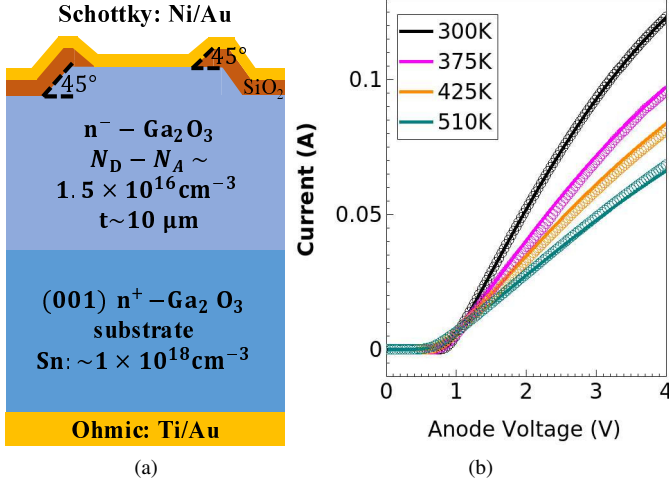


Fig. 1. (a) Structure of the fabricated β -Ga₂O₃ Schottky barrier diodes. (b) Calibration of the TCAD simulation model: experimental (lines) and TCAD simulated (markers) IV curves at different temperatures.

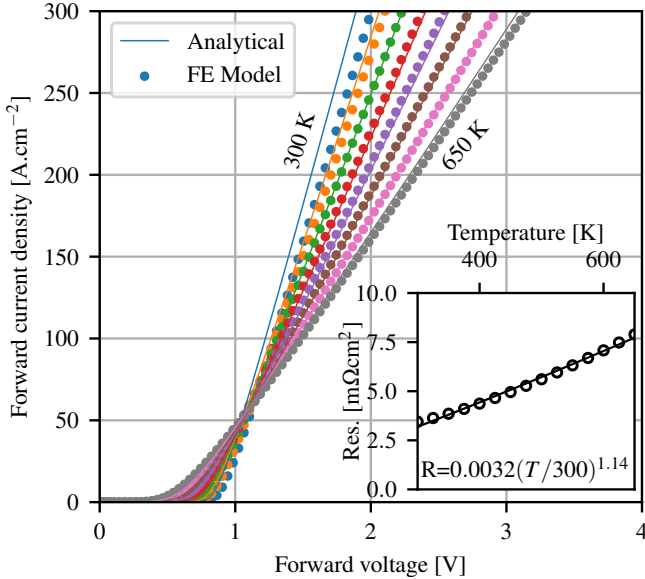


Fig. 2. On-state characteristic of a β -Ga₂O₃ as generated from finite element (TCAD) simulation, and corresponding analytical model, for temperatures ranging from 300 to 650 K. The inset graph presents the change in dynamic resistance as a function of temperature.

is based on the intrinsic properties of the material and on the thermal performance of the associated package.

In this paper, we investigate the evolution of the conduction losses of β -Ga₂O₃ diodes, based on experimental devices fabricated on commercial 2-inch β -Ga₂O₃ wafers (section II). Then we develop an electro-thermal model of the diodes and their packaging (section III), and use this model to predict the surge current behavior of the diodes (section IV).

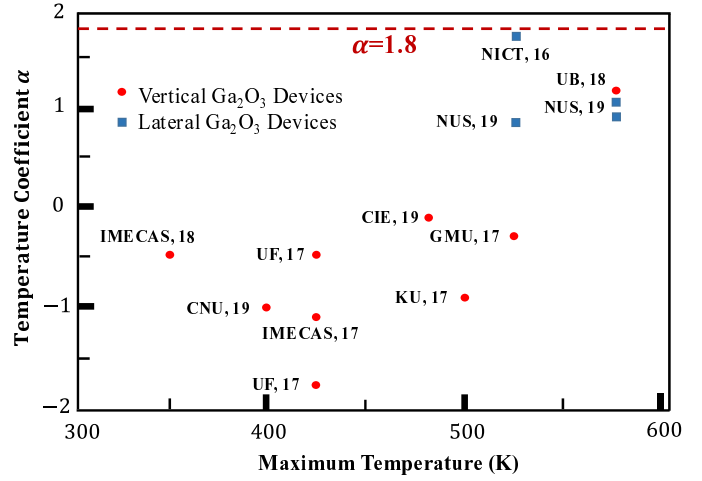


Fig. 3. Value of the temperature-dependence coefficient α for devices published in the literature, as a function of the maximum test temperature (with $R_{on}(T) = R_{300} \left(\frac{T}{300}\right)^\alpha$)

II. EFFECT OF THE TEMPERATURE ON THE FORWARD CHARACTERISTIC OF A β -Ga₂O₃ SCHOTTKY DIODE

To calibrate the electro-thermal simulation models, β -Ga₂O₃ power Schottky barrier rectifiers (SBDs) have been fabricated on 2-inch β -Ga₂O₃ substrates. As shown in Fig. 1a, the epitaxial structure consists of a $\approx 10 \mu\text{m}$ thick Si-doped n-Ga₂O₃ ($N_D \approx 1.5 \times 10^{16} \text{ cm}^{-3}$) grown by HVPE on a commercial 2-inch n⁺-Ga₂O₃ substrate. The detailed device fabrication and performance is reported in [3]. The device I-V and C-V characteristics were measured up to 500 K, and were then used to calibrate the TCAD electro-thermal simulation models (Fig. 1b). The net N_D extracted from C-V characteristics shows nearly no dependence on temperature, indicating that Si is fully ionized in the drift region.

To understand the thermal limit of β -Ga₂O₃ power diodes, a 1.2 kV β -Ga₂O₃ power SBD with an optimal drift region is designed. Here the breakdown voltage (BV) is designed as 1440 V to provide 20% safe margin for voltage rating and the maximum average electric field (E_m) at the Schottky contact is designed as 4 MV cm^{-1} based on the state-of-the-art experimental results [3], [11]. The thickness (t_D) and donor concentration (N_D) are designed based on the non-punch-through model, i.e. $t_D = 2BV/E_m$ and $N_D = qE_m^2/2qBV$, to be $7.2 \mu\text{m}$ and $3.07 \times 10^{16} \text{ cm}^{-3}$, respectively. The I-V characteristics of this optimized 1.2 kV β -Ga₂O₃ power rectifier are then generated by the well-calibrated TCAD simulation up to 650 K.

With the objective of performing simple SPICE transient simulations, an analytical macro model is then fitted to this TCAD model (Fig. 2). This analytical model (forward conduction only) is comprised of two elements. The first is the Schottky junction, represented using a thermionic emission equation [12]:

$$I_F = SA^*T_j^2 e^{\frac{q\Phi_{BN}}{kT_j}} \left(e^{\frac{qV_D}{nkT_j}} - 1 \right) \quad (1)$$

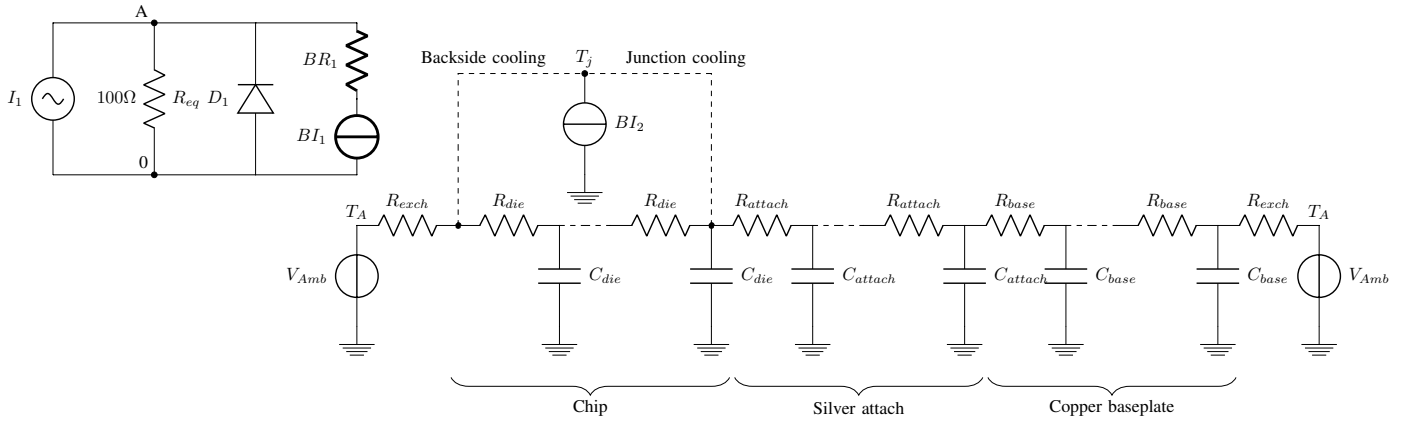


Fig. 4. The electrothermal model used for SPICE simulation: the electrical circuit including the diode model comprised of behavioral elements BI_1 and BR_1 and the thermal network with the power source BI_2 which can be connected to either the top or the bottom surface of the chip.

where S is the junction area, A^* the effective Richardson constant, T_j the junction temperature, q the electronic charge, Φ_{BN} the barrier height, n the ideality factor, V_D the voltage across the junction, k the Boltzmann's constant. The second element of the model corresponds to the electric resistance, mainly of the drift layer and substrate:

$$R_{on}(T_J) = R_{300} \left(\frac{T_J}{300} \right)^\alpha \quad (2)$$

with R_{300} the resistance at 300 K, and α an exponent (in Fig. 2, $\alpha = 1.14$). The value of α appears to vary strongly from one device to another according to the literature. The relation between on-resistance (R_{on}) and the temperature is vital to analyze the thermal stability of power devices [10], [13]. Following the commonly used power law in (2), we extracted the temperature coefficient α in all experimental β -Ga₂O₃ power devices with high-temperature performance in the literature. As shown in Fig. 3, the highest α is close to 1.8 in lightly doped lateral β -Ga₂O₃ thin-film MOSFETs. This α is mainly determined by the temperature dependence of β -Ga₂O₃ mobility, which follows a $T^{-1.5}$ power law as the result of phonon scattering [14], [15]. Much lower or even negative α is shown in vertical β -Ga₂O₃ power devices, which is attributed to the increased donor ionization in the n^+ -Ga₂O₃ substrate at high temperatures [16]. These α dependencies have also been validated by our TCAD simulation. To consider the worst case corresponding to the fastest R_{on} increase with temperature, α is changed from 1.14, which provides the best fitting to our TCAD and experimental data (Fig. 2), to 1.8, with all other parameters in the analytical model remaining unchanged.

III. ELECTRO-THERMAL MODEL OF THE DIODE

The electro-thermal model in Fig. 4 contains two parts. First, the electric circuit, with the sine current source I_1 , resistor R_{eq} (for easier convergence of simulation), diode D_1 (to carry negative currents), and the model of the diode under test. This diode model contains two elements, a behavioral current

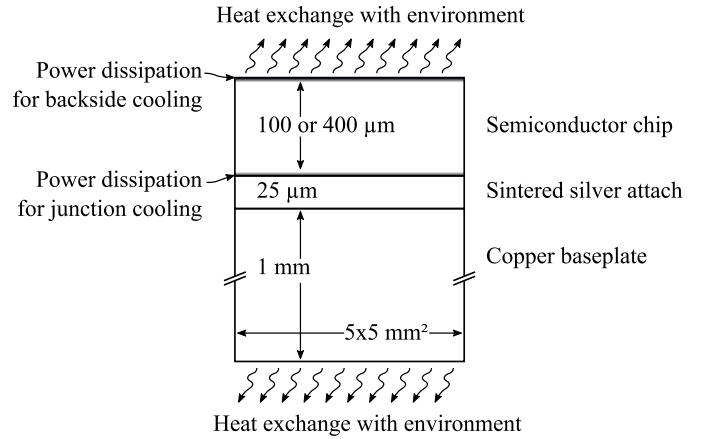


Fig. 5. Packaging structures considered for the electro-thermal analysis.

source BI_1 (to implement (1)) and a behavioral resistance BR_1 (to implement (2)). The second part of the circuit represents the thermal model in the form of a Cauer network.

For the thermal model, two cases are considered (see Fig. 5): the chip is mounted either in the standard way (i.e with the Schottky junction on top), or it is mounted in the "flip-chip" configuration (with the Schottky junction at the bottom of the chip). In the first case, power is dissipated on top of the chip and heat must diffuse through the entire chip thickness before reaching the attach and the baseplate (this is referred to as "backside cooling"). In the second case, the heat dissipated at the Schottky junction has direct access to the attach and baseplate (this is referred to as "junction cooling"). In both cases, a uniform power dissipation is considered at the corresponding surface of the chip. The side surfaces are considered adiabatic. The bottom surface of the baseplate and the top surface of the chip are considered to exchange heat with the environment through a high thermal resistance ($R_{exch} = 100 \text{ K W}^{-1}$). Note that due to the transient nature of the surge current, this thermal resistance has little effect on the results presented below.

TABLE I
PARAMETERS USED FOR THE ELECTROTHERMAL SIMULATIONS

Parameter	Name	Value
Room temp.resistance (arbitrary)	R_{300}	8 m Ω
Temperature coefficient of resistance	α	1.8
Ther. cond. of β -Ga ₂ O ₃ on [001] [5]	$\lambda_{Ga_2O_3}$	14 W m ⁻¹ K ⁻¹
Thermal conductivity of Cu [17]	λ_{Cu}	394 W m ⁻¹ K ⁻¹
Thermal cond. of Sintered Ag [18]	λ_{Cu}	238 W m ⁻¹ K ⁻¹
Specific heat of β -Ga ₂ O ₃ [19]	$c_{pGa_2O_3}$	560 J K ⁻¹ kg ⁻¹
Specific heat of Cu [17]	c_{pCu}	385 J K ⁻¹ kg ⁻¹
Specific heat of Sintered Ag [18]	c_{pCu}	233 J K ⁻¹ kg ⁻¹
Density of β -Ga ₂ O ₃ [1]	ρ_{Cu}	5950 kg m ⁻³
Density of Cu [17]	ρ_{Cu}	8960 kg m ⁻³
Density of Sintered Ag [18]	ρ_{Cu}	8580 kg m ⁻³
Chip thickness (arbitrary)	t_{chip}	100 or 400 μ m
Baseplate thickness (arbitrary)	t_{base}	1 mm
Chip area (arbitrary)	S	25 mm ²
Ambient temperature (arbitrary)	T_A	300 K

For the sake of simplicity, the baseplates and the chip are considered to have the same surface area, so heat spreading effects can be neglected (1-D heat propagation condition). In this case, the chip and baseplates can be subdivided in a series of thermal resistance (R_{Th}) and capacitance (C_{Th}) cells:

$$R_{Th_a} = \frac{t_a}{N_a \lambda_b S} \quad (3)$$

$$C_{Th_a} = \frac{t_a}{N_a} S \rho_b C_{p_b} \quad (4)$$

where subscript a stands for either the baseplate or the chip, and subscript b for the corresponding material (β -Ga₂O₃, Ag or Cu), t_a is the thickness of the element and N_a the number of subdivisions. λ_b the thermal conductivity the corresponding material, ρ_b its density and C_{p_b} its specific heat. S is the chip surface area. The numerical values of these parameters are listed in Tab. I.

In combination the two cooling configuration, two chip thicknesses are considered: 100 and 400 μ m, to investigate the effect of the semiconductor thickness on the surge current behavior. The model from Fig. 4 has been simulated using LTSpice.

Finally, the model from Fig. 4 is also simulated considering SiC instead of β -Ga₂O₃, using the model parameters for a SiC Schottky diode presented in [10]. For the sake of comparison, both β -Ga₂O₃ and SiC diodes are supposed to have a surface area of 0.25 cm² and a nominal resistance (R_{300}) of 8 m Ω . The main difference is the temperature sensitivity of the resistance (α), which was found to be 2.95 for the SiC diode investigated in [10], while it is considered to be 1.8 for β -Ga₂O₃ in the present article.

IV. SIMULATION RESULTS

A transient simulation (Fig.6) shows the calculated temperature rise for a 200 A peak current pulse. This value is chosen as it causes a very high temperature elevation for the 400 μ m-thick chip in backside cooling configuration. It

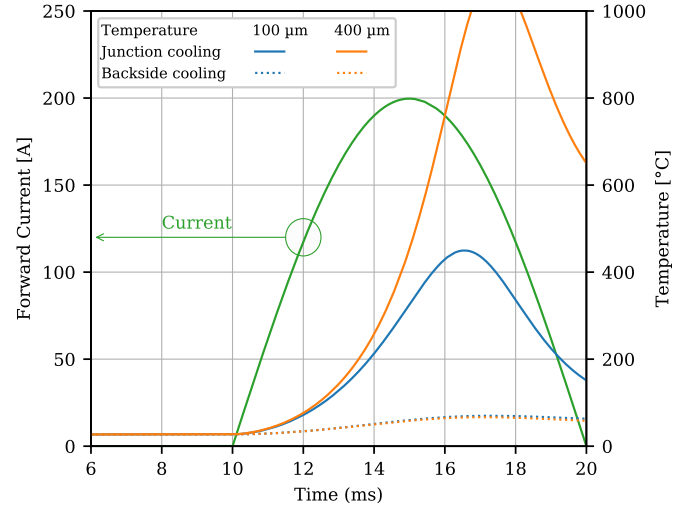


Fig. 6. Temperature transient during a current surge (72 A), for the 4 configuration considered (single or double-side cooling, 100 or 400 μ m-thick chip).

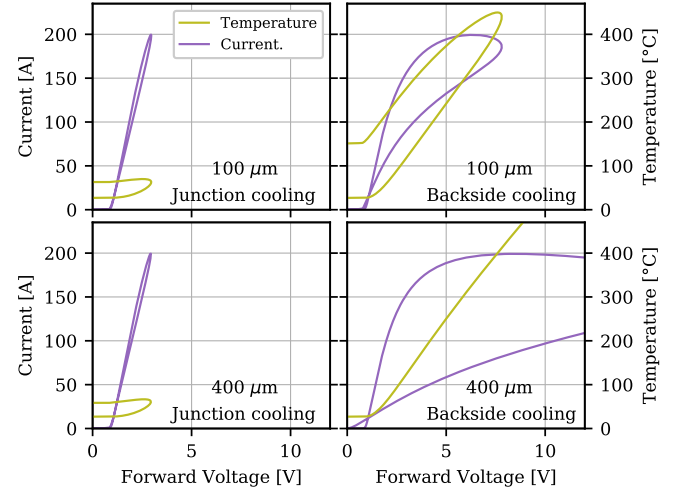


Fig. 7. Temperature transient during a current surge (200 A peak), as a function of the instantaneous forward voltage drop for the 4 configuration considered (single or double-side cooling, 100 or 400 μ m-thick chip).

can be seen that while the temperature only rises moderately for both junction-cooled cases, it increases much more for the backside-cooled cases. For the backside-cooled, 100 μ m-thick chip, the maximum temperature exceeds 300 $^{\circ}$ C, while it exceeds 1000 $^{\circ}$ C for the backside-cooled, 400 μ m-thick chip. This confirms that because of the poor thermal conductivity of β -Ga₂O₃, heat conduction through the chip is limited. Both junction-cooled cases exhibit similar temperature rises, indicating that most of the heat is evacuated through the baseplate, so chip thickness has little influence.

The same data are plotted in Fig. 7, this time as a function of the forward voltage rather than time. Such representation highlights the effects of the increase in forward voltage drop (as the diode heats up) on the power dissipation. As temperature

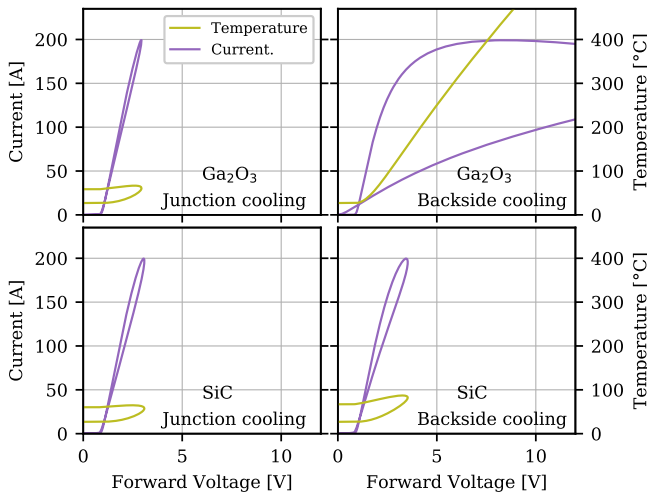


Fig. 8. Temperature transient during a current surge (200 A peak), as a function of the instantaneous forward voltage drop for 400 μm -thick chips with single or double-side cooling, and considering $\beta\text{-Ga}_2\text{O}_3$ or SiC semiconductor material.

increases, so does the forward voltage drop, due to the increase in dynamic resistance, as described by (2). As a result, the power dissipation (the product of forward current and voltage) also increases, causing the temperature to rise further. The rightmost graphs in Fig. 7, which correspond to the backside-cooled cases, illustrate this positive feedback: while the current pulse is identical in all cases, the resulting forward voltage is noticeably different (7 V max. for the 100 μm -thick chip vs. >12 V max. for the 400 μm -thick chip). This means that the elevated junction temperature reached in the backside-cooled, 400 μm -thick chip case (>1000 °C) is the result of both the higher thermal resistance of the thicker chip and of the higher power dissipation due to the positive temperature coefficient of the forward voltage drop.

Regarding the comparison between SiC and $\beta\text{-Ga}_2\text{O}_3$ diodes, the results are summarized in Fig. 8, for 400 μm -thick chips and a surge current of 200 A. Contrarily to the backside-cooled $\beta\text{-Ga}_2\text{O}_3$ diode (top right graph), the SiC diode can sustain the surge event with little temperature rise, even with backside-cooling (bottom graphs). This is due to the much better thermal conductivity of SiC ($390 \text{ W m}^{-1} \text{ K}^{-1}$, as opposed to $14 \text{ W m}^{-1} \text{ K}^{-1}$ for $\beta\text{-Ga}_2\text{O}_3$). When considering junction-cooling (leftmost graphs in Fig. 8), both the SiC and the $\beta\text{-Ga}_2\text{O}_3$ diodes show very similar behavior, with only small temperature rise (a few tens of degree Celsius), as most of the dissipated heat can be absorbed by the chip attach and baseplate.

A more complete comparison between the behavior of SiC and $\beta\text{-Ga}_2\text{O}_3$ diodes is given in Fig. 9. For both materials, backside- and junction-cooled diodes are simulated, considering surge current values ranging from 1 to 500 A. In all cases, the chips are considered to be 400 μm -thick and 25 mm^2 in surface. As expected, backside-cooled chips have the lower surge current capability, and their junction temperature is

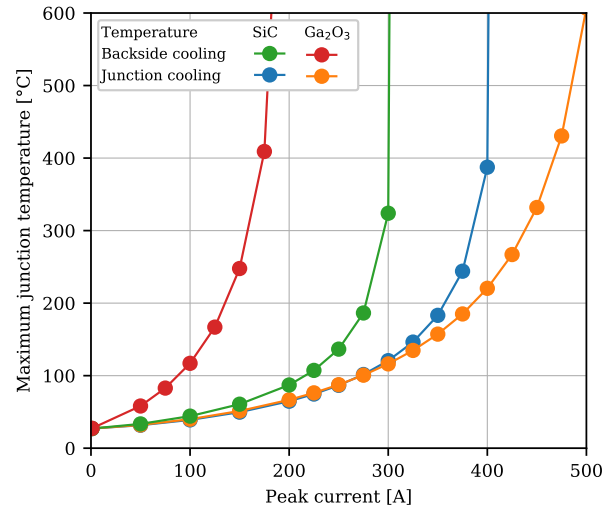


Fig. 9. Maximum temperature reached during a surge event as a function of the peak current, for 400 μm -thick SiC and $\beta\text{-Ga}_2\text{O}_3$ diodes.

found to exceed 600 °C above 175 and 300 A for SiC and $\beta\text{-Ga}_2\text{O}_3$ respectively. Junction-cooled diodes have a higher capability, at 400 and 500 A.

Moreover, it can be seen that the temperature of the junction-cooled $\beta\text{-Ga}_2\text{O}_3$ diode (orange line in Fig. 9) is lower than that of its SiC counterpart for peak currents above 300 A. This is because of the lower α value of $\beta\text{-Ga}_2\text{O}_3$ in eq. 2 compared to SiC (1.8 vs. 2.95): the on-state resistance of the SiC diode increases faster with the temperature, causing the SiC diode to enter thermal run-away sooner. As can be seen in Fig. 9, the slope of the blue curve (junction-cooled, SiC diode) becomes vertical at a peak current of 400 A. This means that any small increase in peak current results in a dramatic increase in junction temperature, and corresponds to thermal runaway condition. On the contrary, even though its temperature becomes very high (600 °C for a peak current of 500 A), the junction-cooled $\beta\text{-Ga}_2\text{O}_3$ diode (orange line in Fig. 9) has not reached thermal runaway yet.

V. CONCLUSION

The poor thermal conductivity of the material has a strong effect on the current carrying capability of $\beta\text{-Ga}_2\text{O}_3$ diodes in a conventional packaging. This is especially true regarding surge current reliability, when the diodes have to sustain a transient increase in current.

Reducing the chip thickness from 400 μm down to 100 μm would reduce the thermal resistance of the chip, albeit not enough to achieve a surge current capability comparable to that of a SiC diode with the same chip size.

“Flipping” the chip, so that its junction would be in direct contact with the copper baseplate is found to be a much more efficient solution, as this removes the thermal resistance of the $\beta\text{-Ga}_2\text{O}_3$ chip entirely. For a peak surge current of 200 A (800 A cm^{-2}), the behaviors of the $\beta\text{-Ga}_2\text{O}_3$ and the SiC diodes are found to be very comparable. For higher peak surge current (above 300 A, or 1200 A cm^{-2}), however, the $\beta\text{-Ga}_2\text{O}_3$

diode exhibits a lower temperature rise and a much more stable behavior: while the SiC diode enter thermal-runaway above 400 A, no such phenomenon is observed for the β -Ga₂O₃ diode. This can be explained by the lower temperature dependency of the on-state resistance (α) of β -Ga₂O₃ as compared to SiC. Note that in this article we considered a high value for α (1.8, see Fig. 3). Lower values would result in an even greater advantage for β -Ga₂O₃.

It can be concluded that the poor thermal conductivity of GaO is partly balanced by its low sensitivity to temperature. β -Ga₂O₃ can be used to build robust devices, with performances comparable to or exceeding those of SiC. However, this requires to change the way the devices are packaged, to provide cooling closer to the heat-dissipating area. Experimental investigations are ongoing to validate this conclusion.

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